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(54) Title: DAMASCENE EXTREME ULTRAVIOLET LITHOGRAPHY (EUVL) PHOTOMASK AND METHOD OF MAKING

(57) Abstract: A photolithography mask for use with extreme ultraviolet lithography (EUVL) irradiation is disclosed. The mask comprises a multilayer stack that is substantially reflective of said EUV irradiation, a supplemental multilayer stack formed atop the multilayer stack, and an absorber material formed in trenches patterned into the supplemental multilayer stack. The absorber material being substantially absorptive EUV irradiation.